

MOS FIELD EFFECT TRANSISTOR

NP88N075CUE,NP88N075DUE,NP88N075EUE,NP88N075KUE

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance $R_{DS(on)} = 8.5 \ m\Omega \ MAX. \ (V_{GS} = 10 \ V, \ I_{D} = 44 \ A)$
- Low Ciss : Ciss = 8200 pF TYP.

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP88N075CUE	TO-220AB
NP88N075DUE	TO-262
NP88N075EUE	TO-263 (MP-25ZJ)
NP88N075KUE	TO-263 (MP-25ZK)

(TO-220AB)



(TO-262)



(TO-263)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vss = 0 V)	VDSS	75	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) Note1	ID(DC)	±88	Α
Drain Current (Pulse) Note2	D(pulse)	±352	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	288	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Single Avalanche Current Note3	IAS	69 / 88	Α
Single Avalanche Energy Note3	Eas	450 / 14	mJ

Notes 1. Calculated constant current according to MAX. allowable channel temperature.

- **2.** PW \leq 10 μ s, Duty cycle \leq 1%
- 3. Starting T_{ch} = 25°C, V_{DD} = 35 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	0.52	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W



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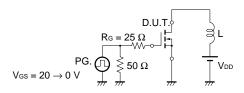
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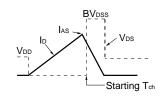


ELECTRICAL CHARACTERISTICS (TA = 25°C)

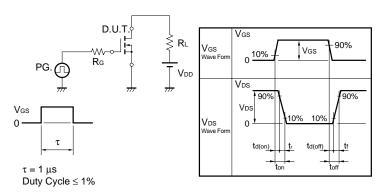
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 75 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0	3.0	4.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 44 A	30	60		S
Drain to Source On-state Resistance	RDS(on)	V _{GS} = 10 V, I _D = 44 A		6.2	8.5	mΩ
Input Capacitance	Ciss	V _{DS} = 25 V		8200	12300	pF
Output Capacitance	Coss	V _{GS} = 0 V		800	1200	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		440	800	pF
Turn-on Delay Time	td(on)	V _{DD} = 38 V, I _D = 44 A		35	77	ns
Rise Time	tr	V _{GS(on)} = 10 V		28	70	ns
Turn-off Delay Time	td(off)	$R_G = 0 \Omega$		105	210	ns
Fall Time	t _f			16	40	ns
Total Gate Charge	QG	V _{DD} = 60 V		150	230	nC
Gate to Source Charge	Qgs	Vgs = 10 V		30		nC
Gate to Drain Charge	Q _{GD}	ID = 88 A		52		nC
Body Diode Forward Voltage	V _{F(S-D)}	IF = 88 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 88 A, VGS = 0 V		80		ns
Reverse Recovery Charge	Qrr	$di/dt = 100 A/\mu s$	_	240		nC

TEST CIRCUIT 1 AVALANCHE CAPABILITY





TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)

Figure 1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

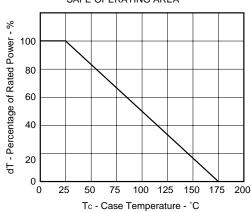


Figure 2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE 350 Total Power Dissipation - W 300 250 200 150 100 Ŗ 50 25 50 75 100 125 150 175 'n

Figure 3. FORWARD BIAS SAFE OPERATING AREA

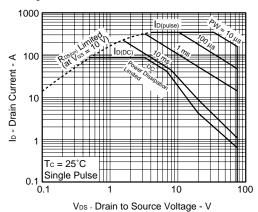
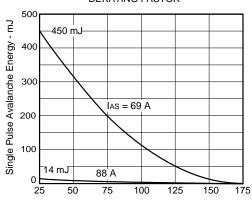


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

Tc - Case Temperature - °C



Starting Tch - Starting Channel Temperature - °C

Figure 5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

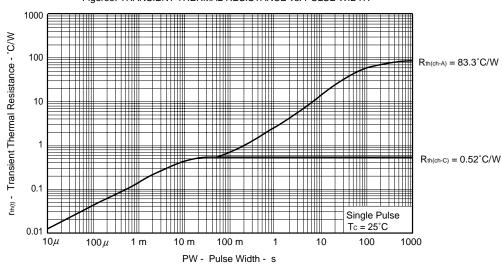


Figure 6. FORWARD TRANSFER CHARACTERISTICS

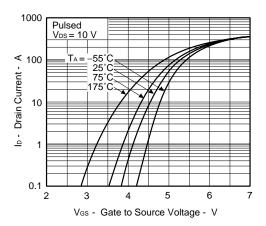


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

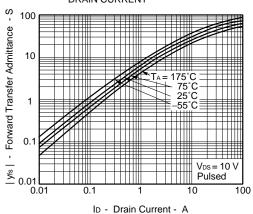
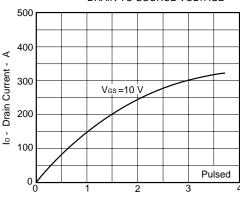


Figure 10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT RDS(on) - Drain to Source On-state Resistance - mΩ Pulsed $V_{GS} = 10$ 0 1000 10 100

ID - Drain Current - A

Figure7. DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

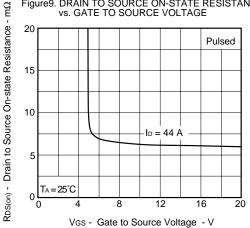
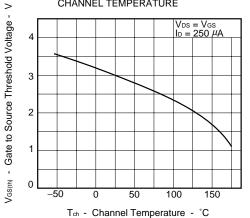
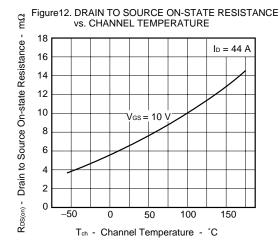
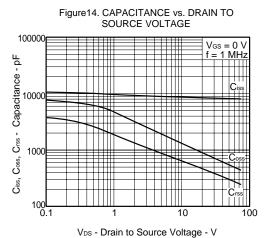
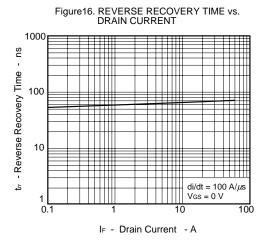


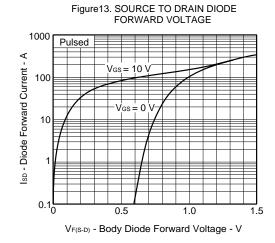
Figure 11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE











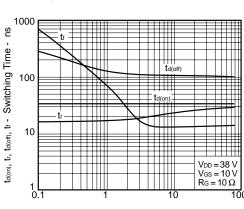
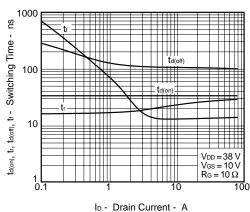
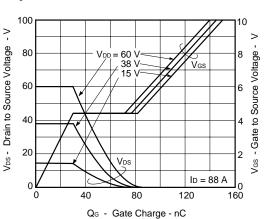


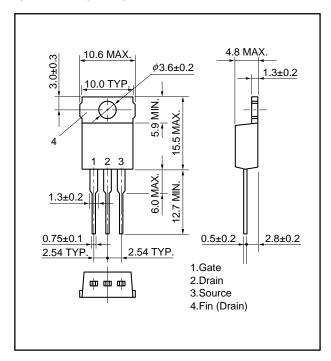
Figure 15. SWITCHING CHARACTERISTICS



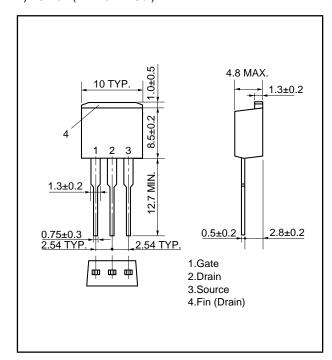


PACKAGE DRAWINGS (Unit: mm)

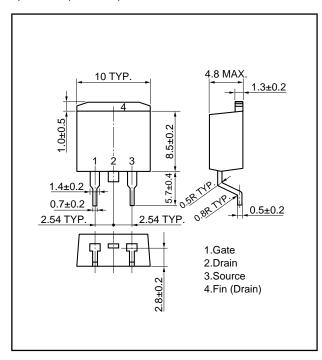
1) TO-220AB (MP-25)



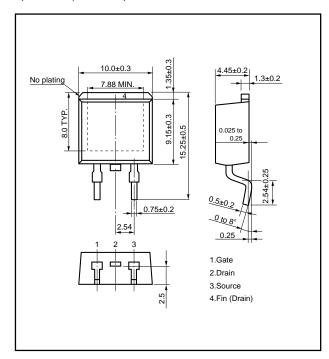
2) TO-262 (MP-25 Fin Cut)



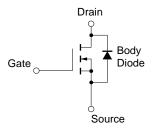
3) TO-263 (MP-25ZJ)



★ 4) TO-263 (MP-25ZK)



EQUIVALENT CIRCUIT



Remark

Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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